

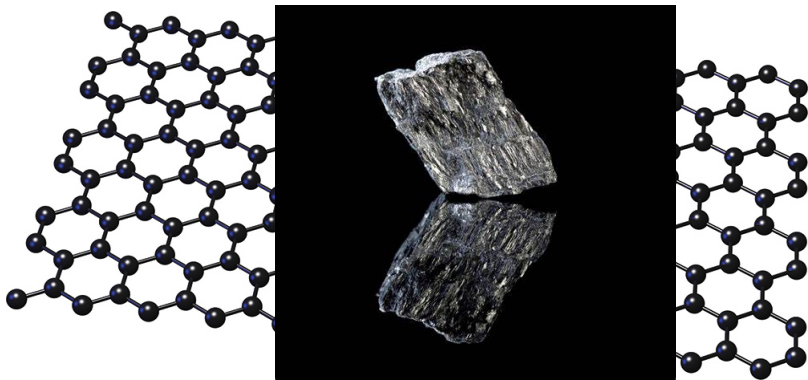
# Graphene based nanoelectronic - a practical approach

or How to fabricate a G-FET

Laboratory of Organic Matter Physics  
University of Nova Gorica

July 7, 2023

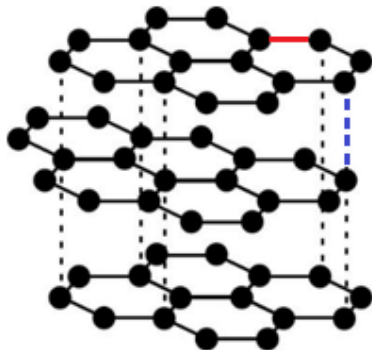
# Graphene



thermofisher.com

B. Terrés, L. Chizhova, F. Libisch, et al. Size quantization of Dirac fermions in graphene constrictions Nat Com. (2016)

# Graphene structure

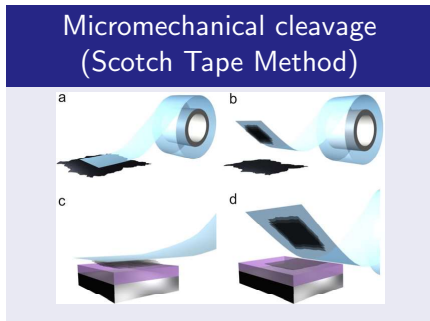


The atomic structure of graphite

- in-plane **covalent** bond:  
bond length=  $0.142\text{nm}$   
bond strength  $\simeq 3.6\text{eV}$
- intra-plane **van der Waals** bond:  
bond length=  $0.335\text{nm}$   
bond strength=  $0.04\text{eV}$

# Fabrication Techniques for Graphene

## Micromechanical cleavage (Scotch Tape Method)

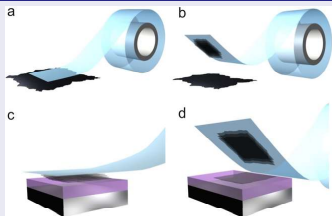


Whitener, Sheehan (2014): "Graphene synthesis.", *Diamond and related materials* 46, 25.

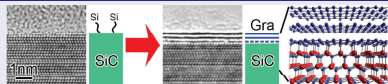
Novoselov, Castro Neto (2012): "Two-dimensional crystals-based heterostructures: materials with tailored properties." *Physica Scripta*, 014006.

# Fabrication Techniques for Graphene

## Micromechanical cleavage (Scotch Tape Method)



## Epitaxial growth on SiC

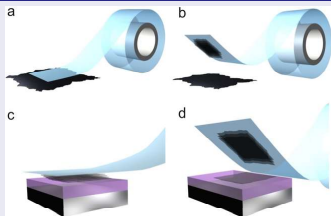


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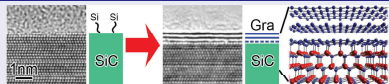
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# Fabrication Techniques for Graphene

## Micromechanical cleavage (Scotch Tape Method)



## Epitaxial growth on SiC



## Chemical Vapor Deposition (CVD)



Whitener, Sheehan (2014): "Graphene synthesis.", *Diamond and related materials* 46, 25.

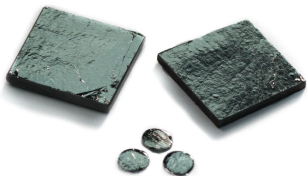
Novoselov, Castro Neto (2012): "Two-dimensional crystals-based heterostructures: materials with tailored properties." *Physica Scripta*, 014006.

# Selection of the parent material

Natural graphite:



Highly oriented pyrolytic graphite (HOPG) :



[2spi.com/category/hopg-spi-supplies/](https://2spi.com/category/hopg-spi-supplies/)

# Selection of the parent material

## Hexagonal Boron Nitride hBN:



- hexagonal lattice structure (similar to Gr): alternating boron (B) and nitrogen (N) atoms;
- dielectric material:  
 $\Delta E_{bandgap} = 5.5 - 6 \text{ eV}$ ;
- weak interlayer bonding (but stronger compared to Gr);
- brittle nature: prone to fracture during exfoliation.



# Selection of the parent material

Molibdenum Disulfide

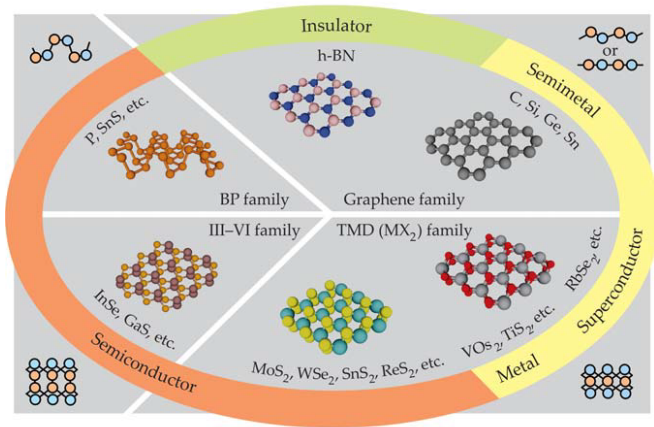
$MoS_2$ :



- hexagonal layered structure (similar to Gr);
- semiconductor:  $\Delta E_g = 1.8$  eV;
- weak interlayer bonding (between Gr and hBN);

# Selection of the parent material

## Other two-dimensional materials



# The substrate

semiconductor



<https://www.mindat.org/min-3659.html>

insulator

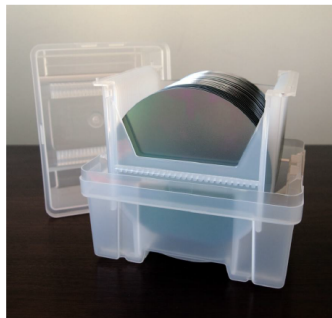


By Parent Géry via Wikimedia Commons

SiO<sub>2</sub>/Si



surface  
oxidation



<https://www.spisemicon.com>

285 nm SiO<sub>2</sub>

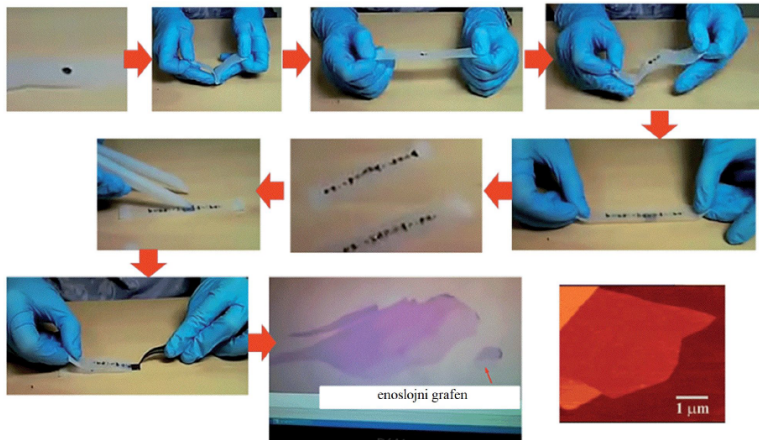
Si

# The micromechanical cleavage

GRAPHITE

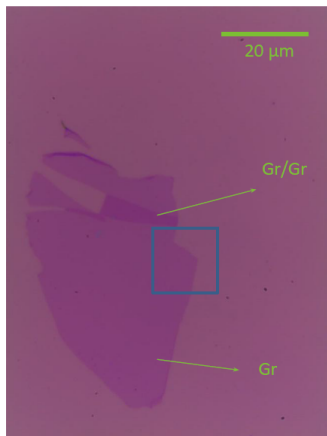
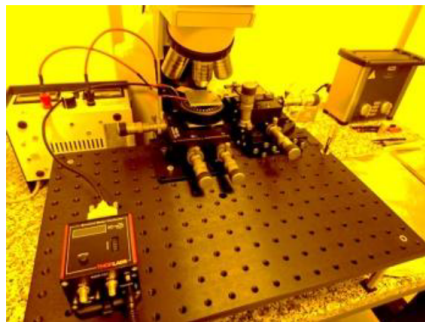
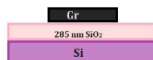


GRAPHENE



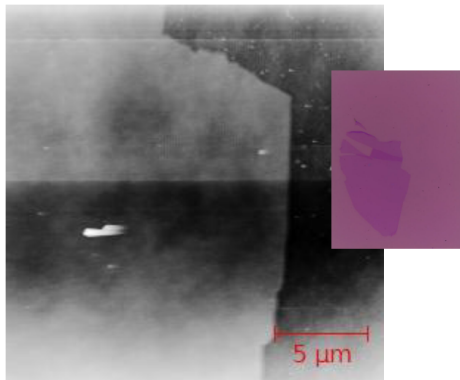
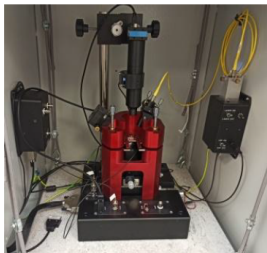
# The characterization

## OPTICAL MICROSCOPY



# The characterization

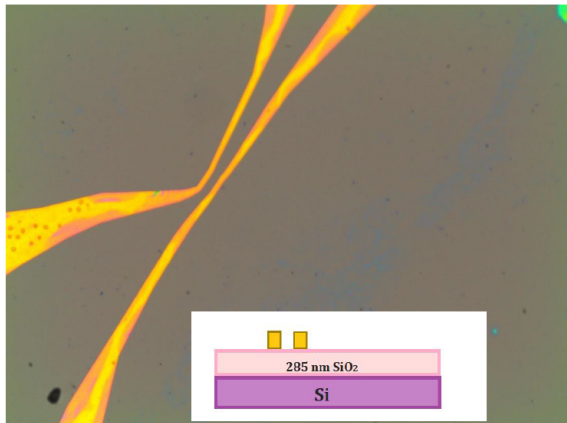
## ATOMIC FORCE MICROSCOPY



# The preparation of the electrodes



## LITHOGRAPHY & EVAPORATION



# The graphene-based field-effect transistor

